

PH100-SI-HA-OD1-D0

Photodiode detector for laser power measurement up to 300 mW.



PRODUCT FAMILY KEY FEATURES

LARGE APERTURES

10 mm Ø for the silicon sensors

3 VERSIONS

- Silicon 350 1080 nm, up to 750 mW
- Silicon-UV 210 1080 nm, up to 38 mW
- Germanium 800 1650 nm, up to 500 mW

CHOICE OF ATTENUATORS

Models with attenuators include a calibration both with and without the removable filter

HIGH ACCURACY

The new PH100-SI-HA presents the lowest calibration uncertainty to date.

PRECISE CALIBRATION

Wavelength selection in 1 nm steps

SMART INTERFACE

Containing all the calibration data

COMPATIBLE STAND

STAND-D-233

SPECIFICATIONS

MEASUREMENT CAPABILITIES	
Maximum average power ¹	300 mW
Noise equivalent power ²	200 pW
Spectral range	400 - 1080 nm
Typical rise time	0.2 s
Power calibration uncertainty ³	±5.0 % (400 - 419 nm) ±4.0 % (420 - 899 nm) ±5.0 % (900 - 1009 nm) ±7.5 % (1010 - 1080 nm)
Peak sensitivity	980 nm
Minimum repetition rate ⁴	155 kHz
 At 1064 nm, with attenuator. See curves for maximum power at other wavelengths. At 980 nm. Nominal value. Actual value depends on environmental electromagnetic interference and wavelength. With attenuator. See user manual for calibration uncertainty without attenuator. See user manual for details. 	

DAMAGE THRESHOLDS

Maximum average power density 100 W/cm² PHYSICAL CHARACTERISTICS 10 mm Aperture diameter Absorber Si 38.1Ø x 36D mm Dimensions Weight 0.14 kg 13.7 mm Distance to sensor face

ORDERING INFORMATION

PH100-Si-HA-OD1-D0

INTERESTED IN THIS PRODUCT?

GET A QUOTE

Find your local sales representative at gentec-eo.com/contact-us